

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

# 2SC2873

POWER AMPLIFIER APPLICATIONS

POWER SWITCHING APPLICATIONS

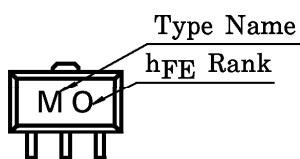
- Low Saturation Voltage :  $V_{CE(sat)} = 0.5V$  (Max.) ( $I_C = 1A$ )
- High Speed Switching Time :  $t_{stg} = 1.0\mu s$  (Typ.)
- $P_C = 1\sim 2W$  (Mounted on Ceramic Substrate)
- Small Flat Package
- Complementary to 2SA1213

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

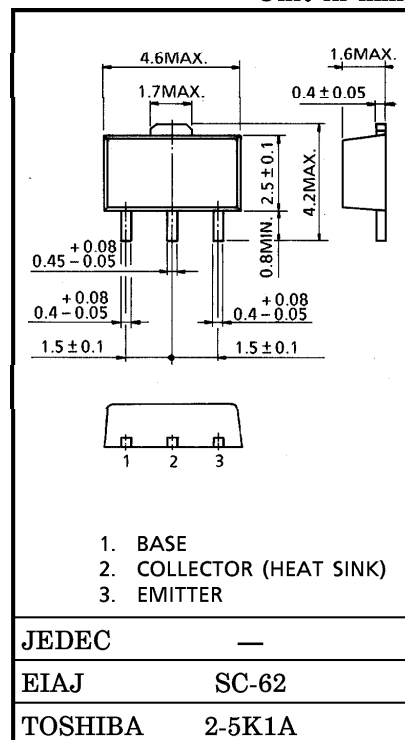
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	50	V
Collector-Emitter Voltage	$V_{CEO}$	50	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	2	A
Base Current	$I_B$	0.4	A
Collector Power Dissipation	$P_C$	500	mW
Collector Power Dissipation	$P_C$ (Note)	1000	mW
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature Range	$T_{stg}$	-55~150	$^\circ C$

(Note) : Mounted on ceramic substrate ( $250mm^2 \times 0.8t$ )

MARKING



Unit in mm



Weight : 0.05g

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT				
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = 50V, I_E = 0$	—	—	0.1	$\mu A$				
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = 5V, I_C = 0$	—	—	0.1	$\mu A$				
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10mA, I_B = 0$	50	—	—	V				
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE} = 2V, I_C = 0.5A$	70	—	240					
	$h_{FE(2)}$	$V_{CE} = 2V, I_C = 2.0A$	20	—	—					
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 1A, I_B = 0.05A$	—	—	0.5	V				
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 1A, I_B = 0.05A$	—	—	1.2	V				
Transition Frequency	$f_T$	$V_{CE} = 2V, I_C = 0.5A$	—	120	—	MHz				
Collector Output Capacitance	$C_{ob}$	$V_{CB} = 10V, I_E = 0, f = 1MHz$	—	30	—	pF				
Switching Time	Turn-on Time	$t_{on}$					—	0.1	—	$\mu s$
	Storage Time	$t_{stg}$					—	1.0	—	
	Fall Time	$t_f$					—	0.1	—	

(Note) :  $h_{FE(1)}$  Classification    O : 70~140,    Y : 120~240

